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|-------------------------------------|---------|
| $r_{DS(ON)}$ (at $V_{GS}=4.5V$) | 55 mohm |
| • $R_{DS(ON)}$ (at $V_{GS}=2.5V$) | 75 mohm |

- Trench Power LV MOSFET technology
- High Density Cell Design for Low $R_{DS(ON)}$
- High Speed switching
- Part no. with suffix “Q” means AEC-Q101 qualified

- Interfacing, Logic switch
- Load switch
- Power management

Drain-source Voltage		V_{DS}	20	-20	V
Gate-source Voltage		V_{GS}	10	10	V
Drain Current	$T_A=25$	I_D	2.0	-1.5	A
	$T_A=100$		1.3	-1.0	

(Example)

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■ (T_J=25 unless otherwise noted)

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Figure1. Output Characteristics

Figure2. Transfer Characteristics

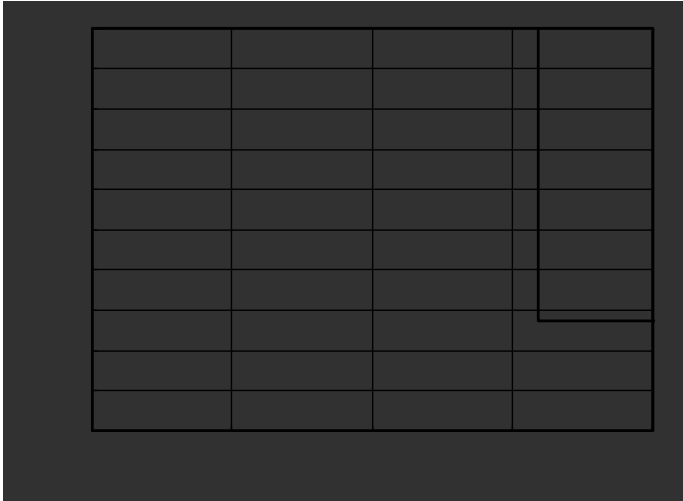


Figure 7. $R_{DS(on)}$ VS Drain Current

Figure 8. Forward characteristics of reverse diode

Figure 9. Normalized breakdown voltage

Figure 10. Normalized Threshold voltage

Figure 11. Maximum Transient Thermal Impedance

Figure 12. Safe Operation Area

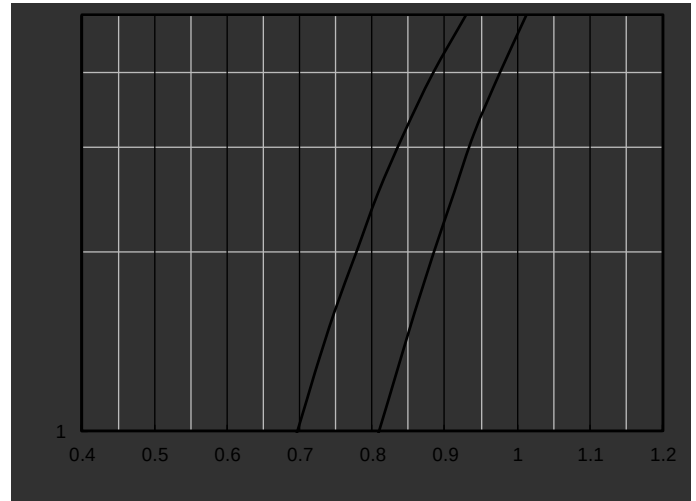


Figure 7. $R_{DS(on)}$ VS Drain Current

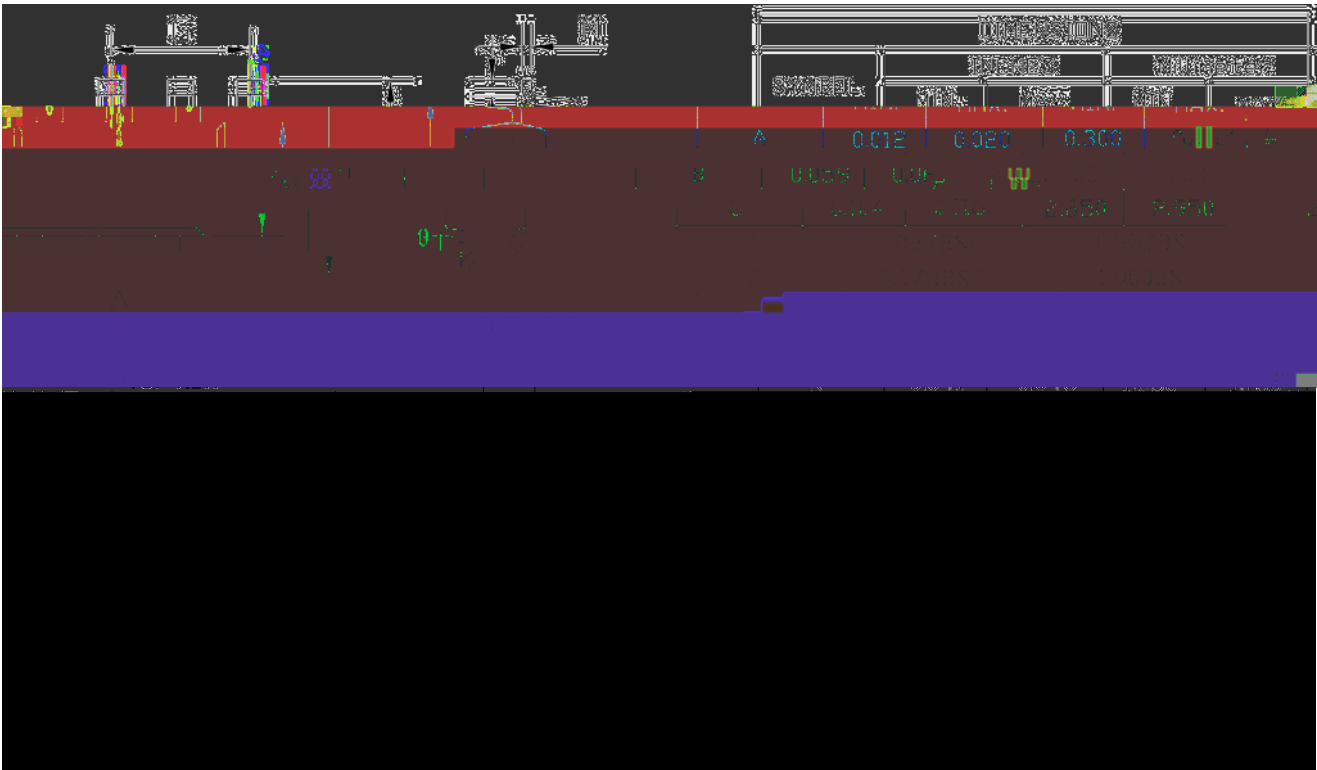
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Figure 11. Maximum Transient Thermal Impedance

Figure 12. Safe Operation Area



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